

MC74VHC1GT04

Inverting Buffer / CMOS Logic Level Shifter

LSTTL–Compatible Inputs

The MC74VHC1GT04 is a single gate inverting buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL–type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic–level translator from 3 V CMOS logic to 5 V CMOS Logic or from 1.8 V CMOS logic to 3 V CMOS Logic while operating at the high–voltage power supply.

The MC74VHC1GT04 input structure provides protection when voltages up to 7.0 V are applied, regardless of the supply voltage. This allows the MC74VHC1GT04 to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when $V_{CC} = 0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- High Speed: $t_{PD} = 3.8$ ns (Typ) at $V_{CC} = 5$ V
- Low Power Dissipation: $I_{CC} = 1$ μ A (Max) at $T_A = 25^\circ$ C
- TTL–Compatible Inputs: $V_{IL} = 0.8$ V; $V_{IH} = 2$ V
- CMOS–Compatible Outputs: $V_{OH} > 0.8 V_{CC}$; $V_{OL} < 0.1 V_{CC}$ @ Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 105; Equivalent Gates = 26
- Pb–Free Packages are Available

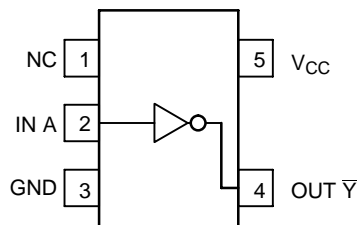


Figure 1. Pinout (Top View)

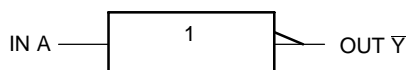


Figure 2. Logic Symbol

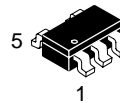
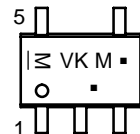


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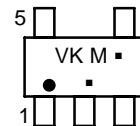
MARKING DIAGRAMS



SC-88A
DF SUFFIX
CASE 419A



TSOP-5
DT SUFFIX
CASE 483



VK = Device Code
M = Date Code*
▪ = Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT

1	NC
2	IN A
3	GND
4	OUT \bar{Y}
5	V_{CC}

FUNCTION TABLE

A Input	\bar{Y} Output
L	H
H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MC74VHC1GT04

MAXIMUM RATINGS

Symbol	Characteristics	Value	Unit
V_{CC}	DC Supply Voltage	-0.5 to +7.0	V
V_{IN}	DC Input Voltage	-0.5 to +7.0	V
V_{OUT}	DC Output Voltage	$V_{CC} = 0$ High or Low State -0.5 to 7.0 -0.5 to $V_{CC} + 0.5$	V
I_{IK}	Input Diode Current	-20	mA
I_{OK}	Output Diode Current	$V_{OUT} < GND; V_{OUT} > V_{CC}$	+20 mA
I_{OUT}	DC Output Current, per Pin	+25	mA
I_{CC}	DC Supply Current, V_{CC} and GND	+50	mA
P_D	Power dissipation in still air	SC-88A, TSOP-5	200 mW
θ_{JA}	Thermal resistance	SC-88A, TSOP-5	333 °C/W
T_L	Lead temperature, 1 mm from case for 10 s	260	°C
T_J	Junction temperature under bias	+150	°C
T_{stg}	Storage temperature	-65 to +150	°C
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 400 N/A V
$I_{Latchup}$	Latchup Performance	Above V_{CC} and Below GND at 125°C (Note 4)	±500 mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD22-A114-A
2. Tested to EIA/JESD22-A115-A
3. Tested to JESD22-C101-A
4. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V_{CC}	DC Supply Voltage	3.0	5.5	V
V_{IN}	DC Input Voltage	0.0	5.5	V
V_{OUT}	DC Output Voltage	$V_{CC} = 0$ High or Low State 0.0 0.0	5.5 V_{CC}	V
T_A	Operating Temperature Range	-55	+125	°C
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 3.3 V \pm 0.3 V$ $V_{CC} = 5.0 V \pm 0.5 V$	0 100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

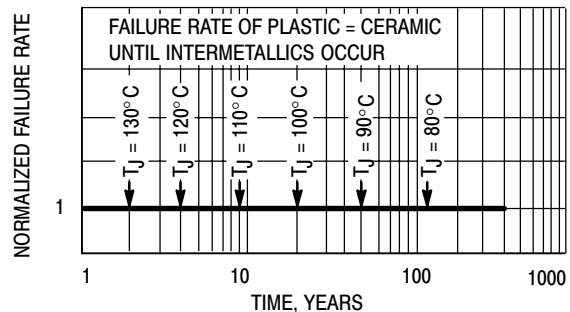


Figure 3. Failure Rate vs. Time Junction Temperature

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		-55 ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0	V	
V _{IL}	Maximum Low-Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4	V	
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -4 mA I _{OH} = -8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66	V	
V _{OL}	Maximum Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 μA	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OL} = 4.0 mA I _{OL} = 8.0 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			1.0		20		40	μA
I _{CC(T)}	Quiescent Supply Current	Input: V _{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μA

AC ELECTRICAL CHARACTERISTICS C_{load} = 50 pF, Input t_r = t_f = 3.0 ns

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A ≤ 85°C		-55 ≤ T _A ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15 pF C _L = 50 pF		5.0 6.2	10.0 13.5		11.0 15.0		13.0 17.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15 pF C _L = 50 pF		3.8 4.2	6.7 7.7		7.5 8.5		8.5 9.5	
C _{IN}	Maximum Input Capacitance			5.0	10		10		10	pF

C _{PD}	Power Dissipation Capacitance (Note 5)	Typical @ 25°C, V _{CC} = 5.0 V		pF
		10		

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

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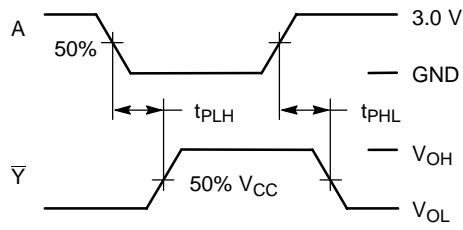
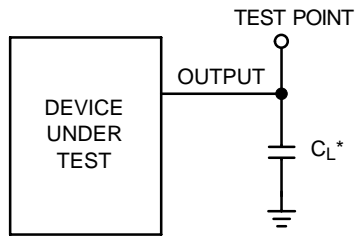


Figure 4. Switching Waveforms



*Includes all probe and jig capacitance

Figure 5. Test Circuit

ORDERING INFORMATION

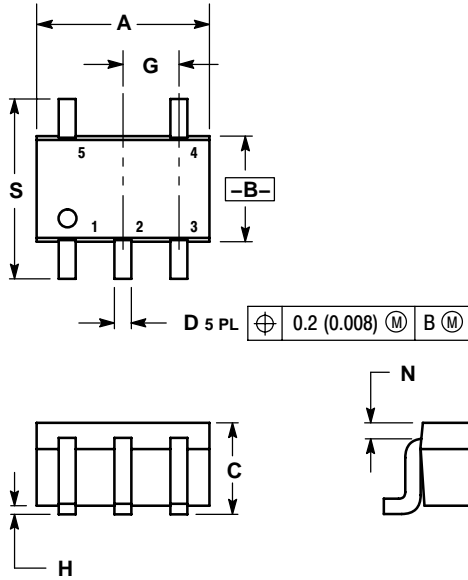
Device	Package Type	Package [†]
MC74VHC1GT04DFT1	SC-88A	3000 / Tape & Reel
M74VHC1GT04DFT1G	SC-88A (Pb-Free)	
MC74VHC1GT04DFT2	SC-88A	
M74VHC1GT04DFT2G	SC-88A (Pb-Free)	
MC74VHC1GT04DTT1	TSOP-5	
M74VHC1GT04DTT1G	TSOP-5 (Pb-Free)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MC74VHC1GT04

PACKAGE DIMENSIONS

SC-88A / SOT-353 / SC-70
CASE 419A-02
ISSUE J

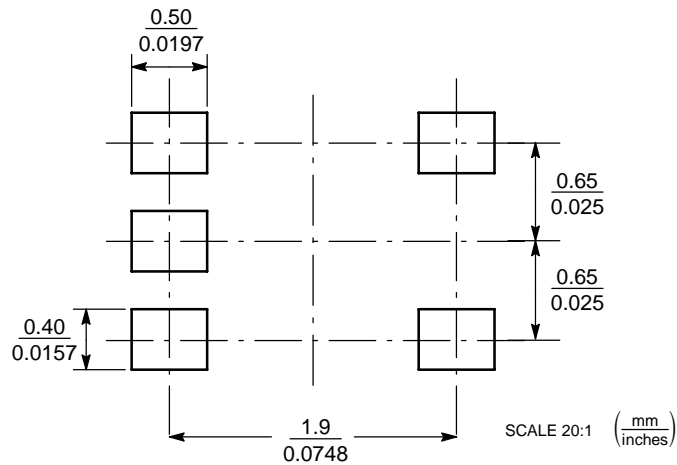


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

SOLDERING FOOTPRINT*

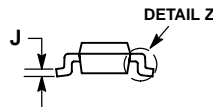
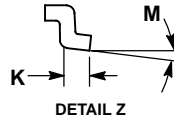
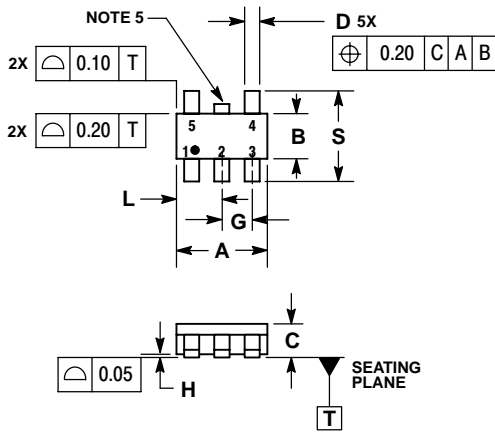


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MC74VHC1GT04

PACKAGE DIMENSIONS

TSOP-5
CASE 483-02
ISSUE F

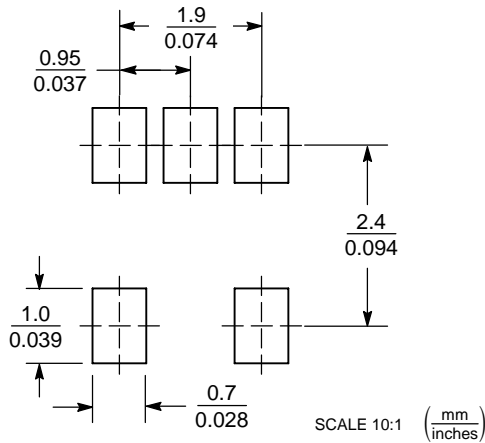


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

DIM	MILLIMETERS	
	MIN	MAX
A	3.00 BSC	
B	1.50 BSC	
C	0.90	1.10
D	0.25	0.50
G	0.95 BSC	
H	0.01	0.10
J	0.10	0.26
K	0.20	0.60
L	1.25	1.55
M	0°	10°
S	2.50	3.00

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.